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Leakage Current Limiting Mechanisms and Ferroelectric

Properties of BiAlO₃/ La_{0.67}Sr_{0.33}MnO₃ Heterostructure

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Abstract: The BiAlO₃/La_{0.67}Sr_{0.33}MnO₃ heterostructure was deposited on LaAlO₃ (111) substrate by pulse laser deposition technology. X-ray diffraction measurement indicates that BiAlO₃ thin films belong to tetragonal phase. Two different leakage current mechanisms, i.e., Space Charge Limited Current and Schottky emission models are observed in *J*–*E* characteristics of BiAlO₃/La_{0.67}Sr_{0.33}MnO₃ heterostructure in different temperature regions, respectively. The ferroelectric hysteresis loops measured by positive-up negative-down method show intrinsic remnant polarization $(2P_r=2.4 \ \mu\text{C/cm}^2)$ at the applied electric field of 750 kV/cm, with the 80 nm thickness of BiAlO₃ thin films at room temperature. The domain imagines and local piezoelectric hysteresis loops obtained by Piezoresponse Force Microscopy technique further reveal the intrinsic ferroelectricity of. BiAlO₃ thin films at room temperature.

Keywords: tetragonal BiAlO₃, the leakage current mechanism, ferroelectricity, PFM

Introduction

Perovskites containing Bi have attracted significant interests for their applications in various fields as lead-free ferroelectric ^[1,2] and multiferroic materials ^[3]. The BiMO₃ oxides (M=Mn, Fe, Al, and In) induce a symmetry-lowering structure with ferroelectricity ^[4] on account of the stereochemically active 6s² lone pair on Bi³⁺. Recently, theoretical studies have reported that BiAlO₃ (BAO) has the possibility of high ferroelectricity with the large spontaneous polarization (P_r) of 75.6 µC/cm² along (111) direction ^[5,6]. Bulk BAO has polar *R3c* symmetry with a=5.38 Å and c=13.40 Å, a ferroelectric transition temperature around 820K, nonmagnetic in intrinsic because of the B-sites occupied by non-magnetic Al ions ^[6,7]. The crystal structure symmetries and P_r direction of BAO resemble the situation observed in BiFeO₃ (BFO) ^[3,8].In Download English Version:

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